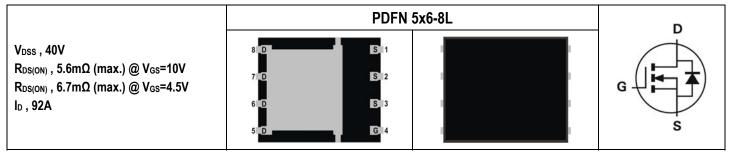


# **SG40N05Q**

40V N-Channel Power MOSFET



Description	Features
The SG40N05Q uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input / Output Leakage</li> <li>Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul> <li>Lithium-Ion Secondary Batteries</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>

### **Ordering Information**

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG40N05Q	Halogen-Free	PDFN 5x6-8L	Q	Tape & Reel	2,500

#### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	40	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current Continuous Note 1	Tc=25°C	L	92	Α
Drain Current-Continuous Note 1	Tc=100°C	lD ID	61	Α
Drain Current-Pulsed Note 1		IDM	220	Α
Durain Counterna Countinuous	T <sub>A</sub> =25°C	1	14	Α
Drain Current-Continuous	T <sub>A</sub> =70°C	ID ID	11	Α
Avalanche Current		las	31	Α
Avalanche Energy, L=0.1mH		Eas	48	mJ
Manimum Davida Diasia atian	Tc=25°C	D D	59.5	W
Maximum Power Dissipation	T <sub>c</sub> =100°C		23.8	W
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

## **Thermal Resistance Ratings**

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	Reja	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	2.1	°C/W



#### Electrical Characteristics (T\_=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	Vgs=0V, Ids=250µA	40	-	-	V
Zero Gate Voltage Drain Current	Idss	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage	lgss	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	Vds=Vgs, Ids=250µA	1.2	-	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>DS</sub> =20A	-	4.8	5.6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =15A	-	6.1	6.7	mΩ

## DYNAMIC CHARACTERISTICS

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	1732	-	
Output Capacitance	Coss	$V_{DS}$ =15V, $V_{GS}$ =0V, f=1MHz	-	356	-	pF
Reverse Transfer Capacitance	Crss		-	148	-	
Gate Resistance	Rg	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	-	1.3	-	Ω

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>		-	23.7	-	
Rise Time	tr	V <sub>DD</sub> =15V, I <sub>D</sub> =30A, V <sub>GEN</sub> =4.5V,	-	20.7	-	
Turn-Off Delay Time	T <sub>d(off)</sub>	$R_{GEN}=1\Omega$ , $R_L=1.5\Omega$	-	24.7	-	ns
Fall Time	t <sub>f</sub>		-	16.8	-	
Total Gate Charge at 10V	Qg		-	11.8	-	
Gate to Source Gate Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A	-	5.9	-	nC
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	4.9	-	

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	Vsd	V <sub>GS</sub> =0V, I <sub>DS</sub> =1A	-	-	1.2	V
Body Diode Reverse Recovery Time	ls		-	-	92	Α
Body Diode Reverse Recovery Charge	I <sub>SM</sub>	$V_G=V_D=0V$ , Force Current	-	-	220	Α
Body Diode Reverse Recovery Time	trr	L = 10.0 dl/dt= 100.0/us T = 25.80	-	26	-	ns
Body Diode Reverse Recovery Charge	Qrr	l⊧=10A, dl/dt=100A/µs, Tյ=25°C	-	18	-	nC

Notes:

1. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

 R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0JC</sub> is guaranteed by design while R<sub>0JA</sub> is determined by the user's board design. R<sub>0JA</sub> shown below for single device operation on FR-4 in still air.





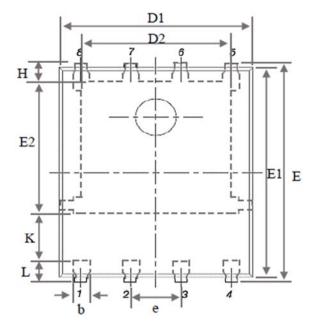
## Marking Information

PDFN 5x6-8L (Q)	Marking Rule
Laser Marking	Line 1 : Device Name
SG40N05Q YYMMXXX Diagram	SG40N05Q <u>Line 2</u> : Date Code YYMMXXX YY : Year Code MM : Month Code XXX : Serial Number

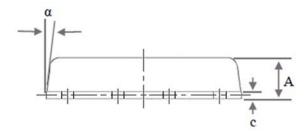


## Package of Dimension





Symbol	Min	Nor	Max
A	0.90	1.04	1.17
b	0.33	0.42	0.51
С	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
е		1.27 BSC	
Н	0.38	0.50	0.61
L	0.38	0.55	0.71
L1	0.05	0.15	0.25

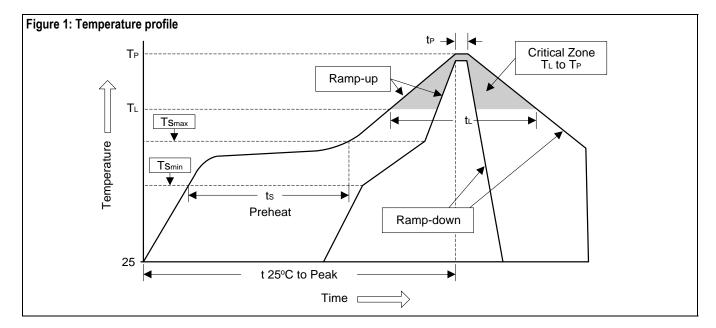






## **Soldering Methods for Silicongear's Products**

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate $(T_L \text{ to } T_P)$	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t <sub>P</sub> )	10 10 300 300	2010 40 300
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

#### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec





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